

PNP SILICON AMPLIFIER TRANSISTOR

Qualified per MIL-PRF-19500/357

Devices

2N3634	2N3635	2N3636	2N3637
2N3634L	2N3635L	2N3636L	2N3637L

Qualified Level

JAN
JANTX
JANTXV
JANS

MAXIMUM RATINGS

Ratings	Symbol	2N3634* 2N3635*	2N3636* 2N3637*	Unit
Collector-Emitter Voltage	V_{CEO}	140	175	Vdc
Collector-Base Voltage	V_{CBO}	140	175	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	1.0		Adc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}\text{C}^{(1)}$		W
		@ $T_C = +25^{\circ}\text{C}^{(2)}$		W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}\text{C}$

*Electrical characteristics for "L" suffix devices are identical to the "non L" corresponding devices

1) Derate linearly 5.71 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly 28.6 mW/ $^{\circ}\text{C}$ for $T_C > +25^{\circ}\text{C}$



TO-39* (TO-205AD)
2N3634, 2N3635
2N3636, 2N3637



TO-5*
2N3634, 2N3635
2N3636, 2N3637

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Current $I_C = 10 \text{ mAdc}$	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	Vdc
Collector-Base Cutoff Current $V_{CB} = 100 \text{ Vdc}$ $V_{CB} = 140 \text{ Vdc}$	2N3634, 2N3635	I_{CBO}	100 10	ηAdc μAdc
Emitter-Base Cutoff Current $V_{EB} = 3.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$		I_{EBO}	50 10	ηAdc μAdc
Collector-Emitter Cutoff Current $V_{CE} = 100 \text{ Vdc}$		I_{CEO}	10	μAdc

ELECTRICAL CHARACTERISTICS (con't)

DYNAMIC CHARACTERISTICS

SAFE OPERATING AREA

$$T_C = 25^{\circ}\text{C}, 1 \text{ Cycle}, t = 1.0 \text{ s}$$
$$V_{CE} = 100 \text{ Vdc}, I_C = 30 \text{ mAdc}$$

$V_{CE} = 130 \text{ Vdc}$, $I_C = 20 \text{ mAdc}$ 2N3636, 2N3637

Test 2

Test 3

3) Pulse Test: Pulse Width = 30

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